



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
Applicant : Ohtani, et al. Art Unit : 2815
Serial No.: 09/379,702 Examiner : Eugene Lee
Filed : August 24, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

BOX AF

Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the action mailed June 21, 2001, please
amend the application as follows:

In the specification:

Please replace the paragraph beginning at page 16, line 4,
with the following rewritten paragraph:

DI -- As shown in Fig. 2(C), dopant ions are implanted into
the active layer 107 by ion implantation techniques, using the
gate electrode 111 and surrounding anodic oxide 112 as a mask.
In order to fabricate a N-channel TFT, phosphorus is introduced.
Using phosphine (PH₃) as a dopant gas, phosphorus ions are
implanted. On the other hand, in order to fabricate a P-channel

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this
correspondence is being deposited with the
United States Postal Service as first class mail
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September 21, 2001

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